

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) An encapsulation structure for a display device, comprising:

a dielectric sealing structure ~~(3)~~, ~~characterized in that the encapsulation structure also comprises a stabilisation that seals protruding structures, the dielectric sealing structure being non-planar and conforming to a shape of the protruding structures; and~~

stabilization layer (5) located over the dielectric sealing structure to form a substantially planar surface.

2. (Currently Amended) ~~An~~ The encapsulation structure according to claim 1, wherein said ~~stabilisation~~ stabilization layer ~~(5)~~ is of a polymeric material.

3. (Currently Amended) ~~An~~he encapsulation structure according to claim 1, wherein said sealing structure ~~(3)~~ comprises a first layer ~~(6)~~ of a first dielectric material and a second layer ~~(7)~~ of a second dielectric material.

4. (Currently Amended) ~~An~~The encapsulation structure according to claim 3, wherein said sealing structure ~~(3)~~further comprises a third layer ~~(8)~~ of a third dielectric material.

5. (Currently Amended) ~~An~~The encapsulation structure according to claim 4, wherein said third dielectric material is the same as said first dielectric material.

6. (Currently Amended) ~~An~~The encapsulation structure according to claim 3, wherein said first dielectric material is selected from the group comprising silicon nitride, aluminium nitride and any mixture thereof, and wherein said second dielectric material is selected from the group comprising silicon oxide,

silicon oxide fluoride, titanium oxide, tantalum oxide, zirconium oxide, hafnium oxide, aluminium oxide and any mixture thereof.

7. (Currently Amended) ~~An~~ The encapsulation structure according to claim 3, wherein said first dielectric material is selected from the group comprising silicon oxide, silicon oxide fluoride, titanium oxide, tantalum oxide, zirconium oxide, hafnium oxide, aluminium oxide and any mixture thereof, and wherein said second dielectric material is selected from the group comprising silicon nitride, aluminium nitride and any mixture thereof.

Claim 8 (Canceled)

9. (Currently Amended) ~~An~~ The encapsulation structure according to claim 1, wherein an essentially cavity-free interface is formed between said ~~stabilisation~~ stabilization layer (5) and said sealing structure ~~(3)~~.

10. (Currently Amended) ~~An~~ The encapsulation structure

according to claim 1, wherein the thermal expansion coefficient of said ~~stabilisation~~stabilization layer (5) is essentially the same as the thermal expansion coefficient of said sealing structure (3).

11. (Currently Amended) ~~An~~The encapsulation structure according to claim 1, wherein the thickness of said ~~stabilisation~~stabilization layer (5) is at least 0.1 μm .

12. (Currently Amended) ~~An~~The encapsulation structure according to claim 1, wherein said encapsulation structure is transparent.

13. (Currently Amended) ~~An~~The encapsulation structure according to claim 1, wherein said ~~stabilisation~~stabilization layer (5) is of a non-polymeric material.

14. (Currently Amended) ~~An~~The encapsulation structure according to claim 13, wherein said non-polymeric material is a cured inorganic material.

Claims 15-19 (Canceled)

20. (Currently Amended) ~~An~~ The encapsulation structure according to claim 1, wherein said display device is selected from a polyLED display, ~~a~~ an OLED display or a Liquid Crystal Display.

21. (Currently Amended) ~~An~~ The encapsulation structure according to claim 1, wherein said ~~display device comprises~~ protruding structures ~~(4) with~~ have negative slopes which ~~forms~~ that form shadow regions.

22. (Currently Amended) A method for ~~the manufacture of~~ manufacturing an encapsulation structure for a display device comprising the acts of:

depositing a dielectric sealing structure ~~(3), and~~ that seals protruding structures, the dielectric sealing structure being non-planar and conforming to a shape of the protruding structures; and

depositing a ~~stabilisation~~ stabilization layer ~~(5)~~ over the

dielectric sealing structure to form a planar surface.

23. (Currently Amended) A The method according to claim 22, wherein said depositing of a ~~stabilisation~~ the stabilization layer (5) comprises depositing a curable composition, and curing said curable composition.

24. (Currently Amended) A The method according to claim 23, wherein said curing is thermal curing.

25. (Currently Amended) A The method according to claim 22 wherein said ~~stabilisation~~ stabilization layer (5) is deposited by inkjet printing.

26. (Currently Amended) A The method according to claim 22 wherein said display device is selected from a polyLED display, an OLED display and a LCD display.

27. (Previously Presented) A display device comprising an

encapsulation structure according to claim 1.

28. (Previously Presented) A display device obtainable by the method according to claim 22.

29. (New) The encapsulation structure of claim 1, wherein the dielectric sealing structure comprises silicon oxide fluoride.

30. (New) The encapsulation structure of claim 1, wherein the stabilization layer comprises Indium.

31. (New) The method of claim 22, further comprising the act of selecting materials for the dielectric sealing structure and stabilization layer such that the materials have substantially equal thermal expansion coefficients.

32. (New) The method of claim 22, wherein the depositing the dielectric sealing structure is performed at 80°C.